



Docket No. 0819-0703

280
#96
25-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of) Art Unit: Unassigned
Yoshiaki HASEGAWA et al.) Examiner: Unassigned
Serial No. 09/993,771)
Filed: November 27, 2001)
For: METHOD FOR MANUFACTURING)
SEMICONDUCTOR AND METHOD)
FOR MANUFACTURING)
SEMICONDUCTOR DEVICE)

CERTIFICATE OF MAILING
I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231, on 3/21/02
[Signature]

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above identified patent application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

On Page 27, First Full Paragraph

Thus, according to the second variation, the etching stop layer **19C** having a super lattice structure is formed under the p-type second cladding layer **20** to be etched, whereby it is possible to control the thickness (remaining thickness) of the p-type first cladding layer **18** with a high precision. As a result, it is possible to obtain a desired thickness, i.e., an optimal value, for the thickness of the p-type first cladding layer **18**. Therefore, the light confinement efficiency in the MQW active layer **15** is significant improved. This is because of the prevention of an etching damage to the MQW active layer **15**.

On Page 30, Fourth Paragraph continuing on Page 31

As illustrated in FIG. 10, during the etching process on the p-type second cladding layer **20**, which is made of p-type $Al_{0.07}Ga_{0.93}N$, the wavelength of the detected PL light is about 350